

SQP3N100C/SQPF3N100C

1000V 3A N-channel Enhancement Mode Power MOSFET

Features

- Lower on-Resistance: $R_{DS(on)}=3.0\Omega$
- Good Stability and Uniformity with High E_{AS}
- 100% Avalanche Test
- Special Process Technology for High ESD Capability

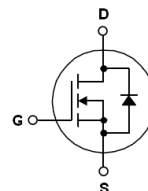
Description

The SQP/PF3N100C is an high blocking voltage N-Channel power MOSFET. This device provide excellent performance for high voltage power supplies or pulse circuits.

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits

Package Type & Internal Circuit



Absolute Maximum Ratings @ $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SQP3N100C	SQPF3N100C	Unit
V_{DSS}	Drain to Source Voltage	1000		V
V_{GSS}	Gate to Source Voltage	± 30		V
I_D	Drain Current	$T_C=25^\circ\text{C}$	3	A
		$T_C=100^\circ\text{C}$	1.8	A
I_{DM}	Pulsed Drain Current (Note1)	12		A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	140	W
	Derate above 25°C	1.12	0.40	W/ $^\circ\text{C}$
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	460		mJ
T_J	Operating Junction Temperature Range	-50~+150		$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50~+150		$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	SQP3N100C	SQPF3N100C	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	0.89	2.97	$^\circ\text{C/W}$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	62.5	62.5	$^\circ\text{C/W}$

Electrical Characteristics @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	1000	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	3.0	4.0	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =1.5A	-	3.0	3.4	Ω
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =V _{DSS} , V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate to Source Leakage Current	V _{GS} =V _{GSS} , V _{DS} =0V	-	-	±100	nA

D-S Diode Characteristics and Maximum Rating @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Maximum Drain to Source Diode Forward Current		-	-	3	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =3A	-	0.85	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =3A,	-	540	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=-100A/us	-	5.2	-	nC

Switching Characteristics @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on Delay Time	I _D =3A , V _{DD} =500V, R _G =25Ω (Note 3)	-	26	58	ns
t _r	Turn-on Rise Time		-	41	92	ns
t _{d(off)}	Turn-off Delay Time		-	40	82	ns
t _f	Turn-off Fall Time		-	32	75	ns
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1.0MHz	-	975	1100	pF
C _{oss}	Output Capacitance		-	78	100	pF
C _{rss}	Reverse Transfer Capacitance		-	2	4.5	pF
Q _g	Total Gate Charge	I _D =3A, V _{DD} =800V V _{GS} =10V (Note 3)	-	17	22	nC
Q _{gs}	Gate to Emitter Charge		-	4.5	-	nC
Q _{gd}	Gate to Collector Charge		-	7.0	-	nC

Note:

1. Repetitive rating: pulse-width limited by maximum junction temperature
2. L=100mH, I_D=3A, V_G=10V, V_{DD}=50V
3. Essentially independent of operating temperature typical characteristics

Typical Performance Characteristics

Fig. 1. Typical on-Resistance Characteristics

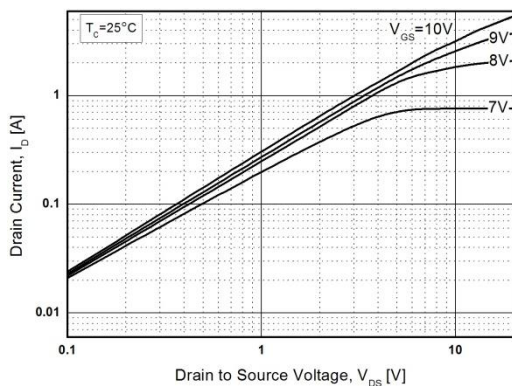


Fig. 2. Typical Transfer Characteristics

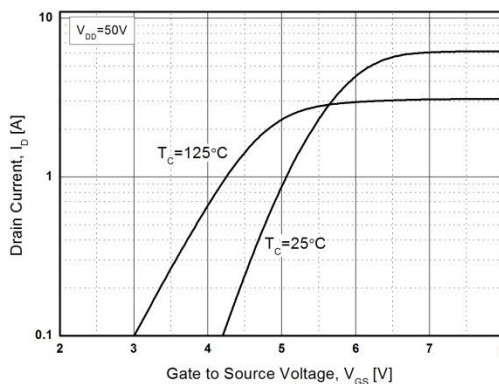


Fig. 3. Static on-Resistance vs. I_D

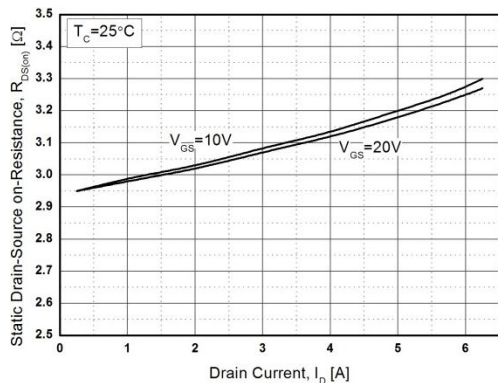


Fig. 4. Body Diode Forward Voltage vs. I_{DR}

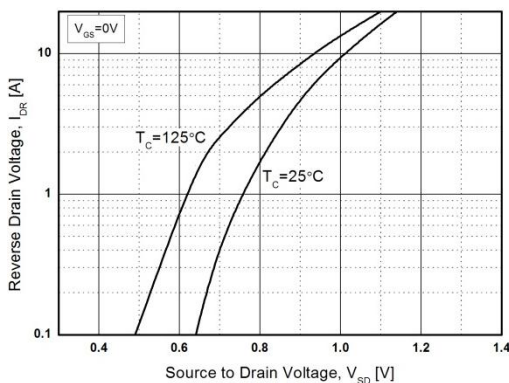


Fig. 5. Capacitance Characteristics

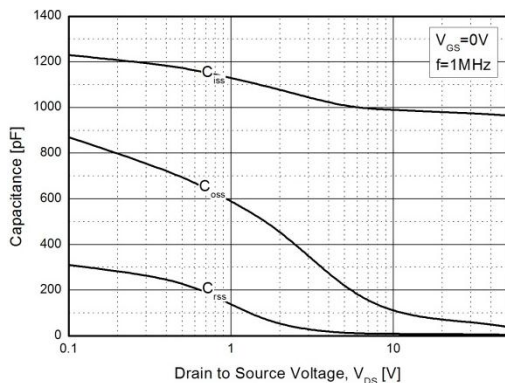
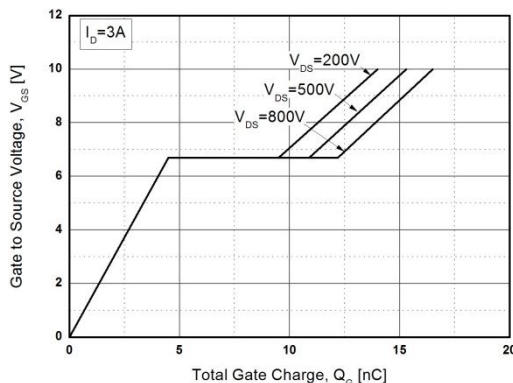


Fig. 6. Gate Charge Characteristics



Typical Performance Characteristics

Fig. 7. Breakdown Voltage vs. Temperature

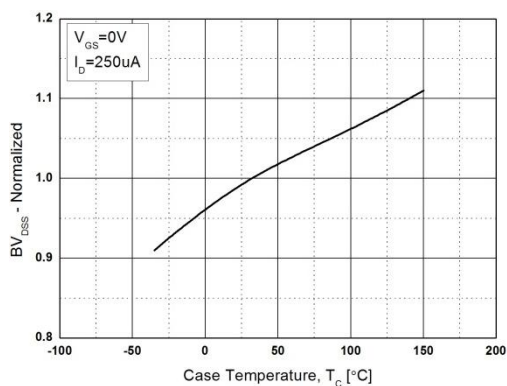


Fig. 8. Static on-Resistance vs. Temperature

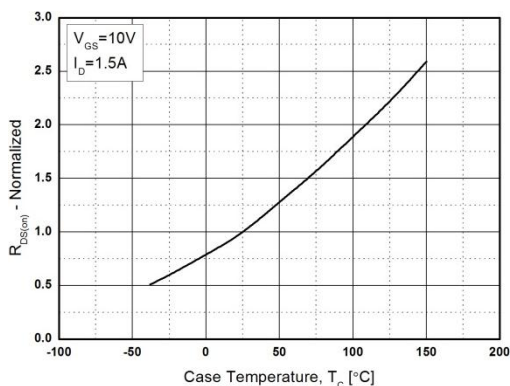


Fig. 9. Maximum Safe Operating Area-SQP3N100C

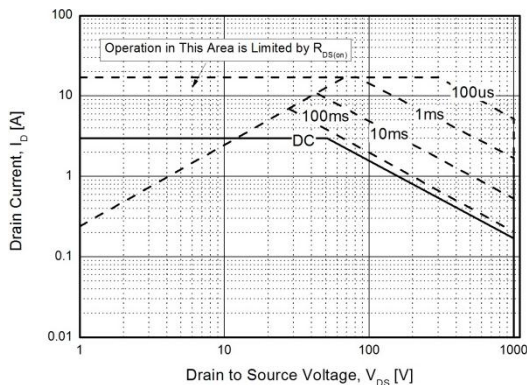


Fig. 10. Maximum Safe Operating Area-SQPF3N100C

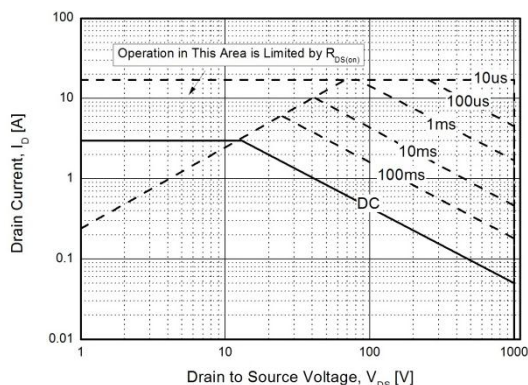
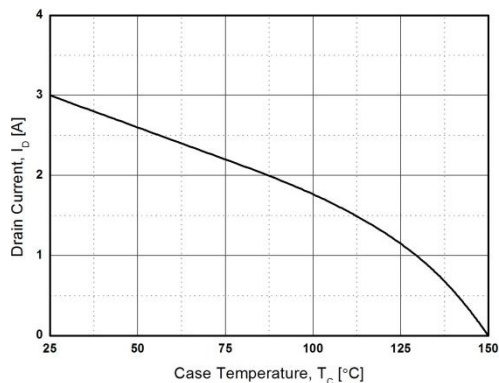


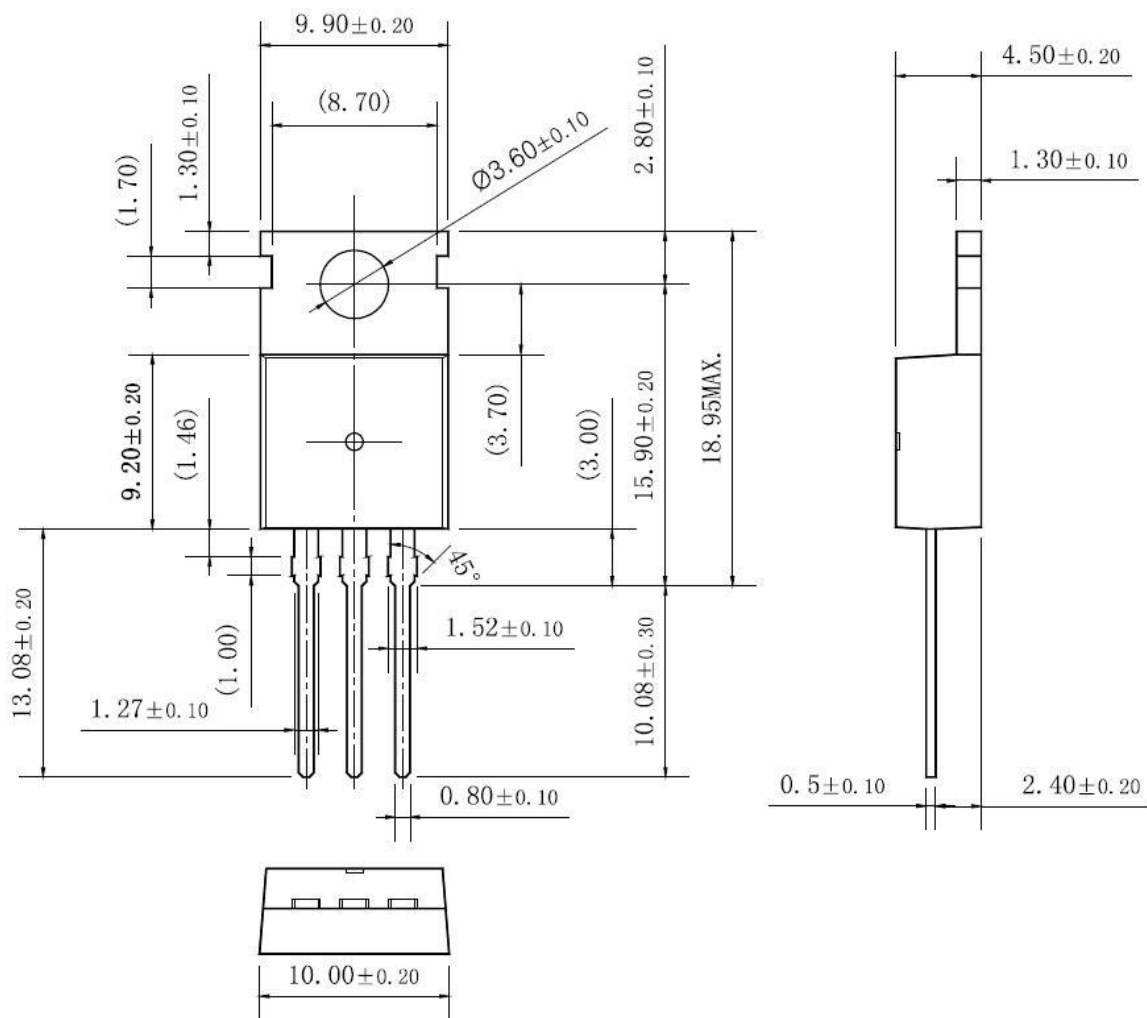
Fig. 11. Maximum Drain Current vs. Temperature



Package Dimensions

TO-220

(Dimensions in Millimeters)



Package Dimensions

TO-220F

(Dimensions in Millimeters)

